## **WEST Search History**



DATE: Friday, March 19, 2004

Hide?	Set Name	Query	Hit Count
	DB=PGF	PB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; O	P=OR
	L36	134 and 111	57
	L35	134 and 111	57
. 🗀	L34	channel adj7 oxide	15617
	L33	cahnnel adj4 oxide	0
	L32	cahnnel adj4 oxide	0
	L31	5216262	22
	DB=PGF	PB, USPT, USOC, EPAB, JPAB, DWPI, TDBD; PLUR=	YES; OP=OR
	L30	5216262	22
	L29	6472685	3
	DB=EPA	B; PLUR=YES; OP=OR	
	L28	2347520	1.
	DB=DW	PI; PLUR=YES; OP=OR	
	L27	L26 and 125	2
	L26	tsu.inv.	-80
	L25	L24 and 123	63
Ċ	L24	barrier and silicon	5445
	L23	wang.inv.	40396
	L22	02103767	. 0
	L21	02/103767	. 0
	DB=PGI	PB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; O	P=OR
	L20	11 and 119	8
	L19	ll 1 adj20 l18	655
	L18	oxide or nitride o fluorine or carbon or carbide	6180325
	L17	6699771	1
	L16	12 and 114 and 115	16
	L15	oxygen or o?sub.\$	811012
	L14	silicon or si	1786914
	L13	17 and 15	56
	L12	11.1 and 118	0
	L11	superlattice	7764
	L10	12 and 18	0

Ē	L9	band-modif\$5	0
	L8	band adj modif\$5	262
	L7	band adj modif\$5 or band-modi\$4	262
	L6	12 and 15	36
	L5	monolayer mono\$5 or atom\$5	1483361
	L4	L3 and 12	27
	L3	parallel	2304355
	L2	superlattice adj6 channel	104
	L1	superlattice adj6 channel	104

END OF SEARCH HISTORY

## Refine Search

#### Search Results -

Terms	Documents			
L18 and L17	2			

US Pre-Grant Publication Full-Text Database

US Patents Full-Text Database

US OCR Full-Text Database

EPO Abstracts Database

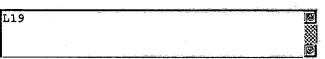
JPO Abstracts Database

Derwent World Patents Index

IBM Technical Disclosure Bulletins

Search:

Database:









#### **Search History**

## DATE: Friday, March 19, 2004 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
•	PLUR=YES; OP=OR		
<u>L19</u>	L18 and 117	2	<u>L19</u>
<u>L18</u>	lofgren.inv.	172	<u>L18</u>
<u>L17</u>	L16 and 115	20	<u>L17</u>
<u>L16</u>	wang.inv.	40396	<u>L16</u>
<u>L15</u>	tsu.inv.	80	<u>L15</u>
<u>L14</u>	2103767	. 7	<u>L14</u>
<u>L13</u>	02103767	0	<u>L13</u>
DB=PGPB,	USPT,EPAB,JPAB,DWPI,T	DBD; PLUR=YES; OP=OR	
<u>L12</u>	11 near20 12	5	<u>L12</u>
<u>L11</u>	L10 near10 11	34	<u>L11</u>
<u>L10</u>	tilt	166799	<u>L10</u>
<u>L.9</u>	11 and 18	. 4	<u>L9</u>
<u>L8</u>	5679152	55	<u>L8</u>
<u>L7</u>	13 and 16	154	<u>L7</u>

# **WEST Search History**

## Restore: Glear Gancel.

DATE: Friday, March 19, 2004

Hide? Set Name Query							
DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR							
	L20	11 and 119	8				
	L19	111 adj20 118	655				
	L18	oxide or nitride o fluorine or carbon or carbide	6180325				
	L17	6699771	1				
	L16	12 and 114 and 115	16				
	L15	öxygen ör o?sub.\$	811012				
	L14	silicon or si	1786914				
	L13	17 and 15	56				
	L12	111 and 118	0				
	L11	superlattice	7764				
	L10	12 and 18	0				
	L9	band-modif\$5	0				
	L8	band adj modif\$5	262				
	L7	band adj modif\$5 or band-modi\$4	262				
	L6	12 and 15	36				
	L5	monolayer mono\$5 or atom\$5	1483361				
	L4	L3 and 12	27				
	L3	parallel	2304355				
	L2	superlattice adj6 channel	104				
	L1	superlattice adj6 channel	104				

**END OF SEARCH HISTORY** 

### Hit List



#### Search Results - Record(s) 1 through 16 of 16 returned.

☐ 1. Document ID: US 6559469 B1

Using default format because multiple data bases are involved.

L16: Entry 1 of 16

File: USPT

May 6, 2003

US-PAT-NO: 6559469

DOCUMENT-IDENTIFIER: US 6559469 B1

TITLE: Ferroelectric and high dielectric constant transistors

DATE-ISSUED: May 6, 2003

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY Paz de Araujo; Carlos A. Colorado Springs CO McMillan; Larry D. Colorado Springs CO Joshi; Vikram Colorado Springs CO Solayappan; Narayan Colorado Springs CO Cuchiaro; Joseph D. Colorado Springs CO

US-CL-CURRENT: <u>257/15</u>; <u>257/16</u>, <u>257/17</u>, <u>257/18</u>, <u>257/19</u>, <u>257/20</u>, <u>257/21</u>, <u>257/22</u>, <u>257/295</u>, <u>257/E21.011</u>, <u>257/E21.272</u>, <u>257/E27.085</u>, <u>257/E27.104</u>

Full	Title	Citation	Frent	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC	Drawe De
						-						

☐ 2. Document ID: US 6426536 B1

L16: Entry 2 of 16

File: USPT

Jul 30, 2002

US-PAT-NO: 6426536

DOCUMENT-IDENTIFIER: US 6426536 B1

TITLE: Double layer perovskite oxide electrodes

Full Title Citation Front Review Classification Date Reference Sequences Affectments Claims KiMC Draw De

☐ 3. Document ID: US 6355951 B1

L16: Entry 3 of 16

File: USPT

Mar 12, 2002

US-PAT-NO: 6355951

DOCUMENT-IDENTIFIER: US 6355951 B1

TITLE: Field effect semiconductor device

☐ 4. Document ID: US 6294446 B1

L16: Entry 4 of 16

File: USPT

Full Title Citation Front Review Classification Date Reference Scattering Anadynamic Claims KMC Draw De

Sep 25, 2001

US-PAT-NO: 6294446

DOCUMENT-IDENTIFIER: US 6294446 B1

TITLE: Methods of manufacturing a high electron mobility transistor with a T-shaped gate electrode

Full Title Citation Front Review Classification Date Reference SEQUENCES LITERATURE Claims KMC Draw. D.

☐ 5. Document ID: US 5952672 A

L16: Entry 5 of 16

File: USPT

Sep 14, 1999

US-PAT-NO: 5952672

DOCUMENT-IDENTIFIER: US 5952672 A

TITLE: Semiconductor device and method for fabricating the same

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KMC Draw De

☐ 6. Document ID: US 5760418 A

L16: Entry 6 of 16

File: USPT

Jun 2, 1998

US-PAT-NO: 5760418

DOCUMENT-IDENTIFIER: US 5760418 A

TITLE: GaAs power semiconductor device operating at a low voltage and method for

fabricating the same

Full Title Citation Front Review Classification Date Reference SCOUCHES Attributed Claims KMC Draw De

☐ 7. Document ID: US 5639677 A

L16: Entry 7 of 16

File: USPT

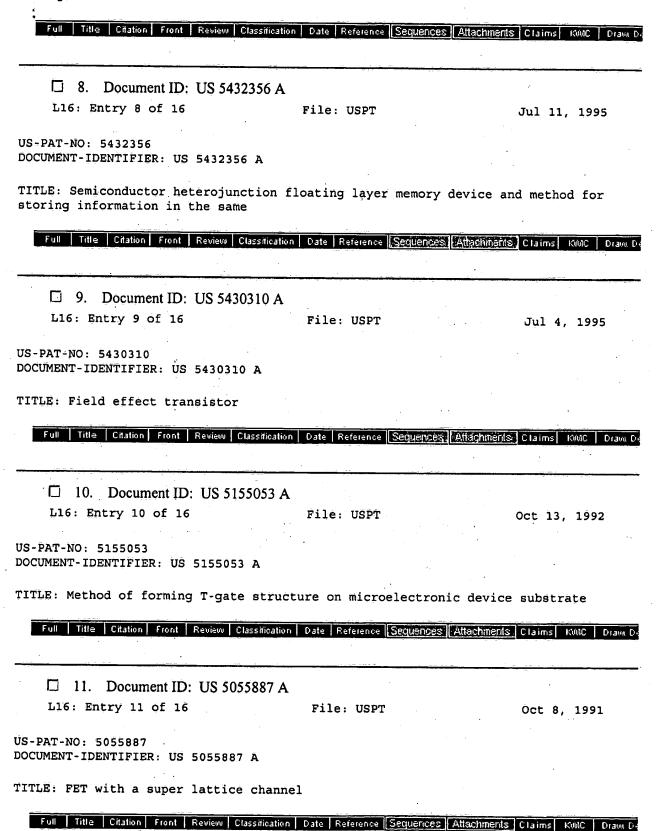
Jun 17, 1997

US-PAT-NO: 5639677

DOCUMENT-IDENTIFIER: US 5639677 A

TITLE: Method of making a gaAs pow r semiconductor device operating at a low

voltage



☐ 12. Document ID: US 5021839 A

L16: Entry 12 of 16

File: USPT

Jun 4, 1991

US-PAT-NO: 5021839

DOCUMENT-IDENTIFIER: US 5021839 A

TITLE: FET with a super lattice channel

Full Title Citation Front Review Classification Date Reference (Section Citation Claims KMC Draw De

☐ 13. Document ID: US 5008211 A

L16: Entry 13 of 16

File: USPT

Apr 16, 1991

US-PAT-NO: 5008211

DOCUMENT-IDENTIFIER: US 5008211 A

TITLE: Method for forming FET with a super lattice channel

Full Title Citation Front Review Classification Date Reference Sections Attainments Claims KWAC Draw. De

☐ 14. Document ID: US 4945393 A

L16: Entry 14 of 16

File: USPT

Jul 31, 1990

US-PAT-NO: 4945393

DOCUMENT-IDENTIFIER: US 4945393 A

TITLE: Floating gate memory circuit and apparatus

Full Title Citation Front Review Classification Date Reference Reference Attended Attended Claims KWIC Draw De

☐ 15. Document ID: US 4905063 A

L16: Entry 15 of 16

File: USPT

Feb 27, 1990

US-PAT-NO: 4905063

DOCUMENT-IDENTIFIER: US 4905063 A

TITLE: Floating gate memories

Full Title Chation Front Review Classification Date Reference Saguetinas Affacations Claims KVIIIC Draw De

☐ 16. Document ID: US 4799087 A

L16: Entry 16 of 16

File: USPT

Jan 17, 1989

US-PAT-NO: 4799087